

**AMENDMENTS TO THE CLAIMS**

1. (cancelled)

2. (currently amended) ~~The method of claim 1, further comprising:~~ A method for controlling the linewidth of a feature formed within a lithography mask, the method comprising:

electrochemically depositing an additive material on exposed sidewalls of an etched first layer of the mask, wherein the top of said etched first layer remains covered by a hardmask used during the etching of said first layer, and wherein a second layer beneath said etched first layer is resistant to the electrochemical deposition of said additive material thereupon;

removing said hardmask; and

etching said second layer with a resulting pattern defined by said etched first layer plus said additive material.

3. (original) The method of claim 2, wherein said electrochemically depositing said additive material further comprises an electroless deposition process.

4. (original) The method of claim 2, wherein said electrochemically depositing said additive material further comprises an electroplating process

5. (currently amended) The method of claim 12, wherein:  
said first layer comprises an optically opaque layer; and  
said second layer comprises a buffer layer between said first layer and a reflective layer underneath said second layer.

6. (currently amended) The method of claim 12, wherein:  
said first layer comprises one of a nickel and a cobalt nickel alloy layer;

said second layer comprises a tantalum nitride layer; and  
said hardmask further comprises a dielectric layer.

7. (cancelled)

8. (original) ~~The method of claim 7, further comprising:~~ A method for controlling the linewidth in an extreme ultraviolet lithography (EUVL) mask, the method comprising:

electrochemically depositing an additive material on exposed sidewalls of an etched absorber layer of the mask, wherein the top of said etched absorber layer remains covered by a hardmask used during the etching of said etched absorber layer, and wherein a buffer layer beneath said etched absorber layer is resistant to the electrochemical deposition of said additive material thereupon;

removing said hardmask; and

etching said buffer layer with a resulting pattern defined by said absorber first layer plus said additive material.

9. (original) The method of claim 8, wherein said electrochemically depositing said additive material further comprises an electroless deposition process.

10. (original) The method of claim 8, wherein said electrochemically depositing said additive material further comprises an electroplating process.

11. (currently amended) The method of claim 7~~8~~, wherein:  
said absorber layer comprises an optically opaque layer; and  
said buffer layer is disposed between said absorber layer and a multilayer (ML) reflective layer underneath said buffer layer.

12. (currently amended) The method of claim 7~~8~~, wherein:

said absorber layer comprises one of a nickel and a cobalt nickel alloy layer;  
said buffer layer comprises a tantalum nitride layer; and  
said hardmask further comprises a dielectric layer.

13. (original) The method of claim 12, wherein said ML reflective layer further comprises alternating layers of molybdenum (Mo) and silicon (Si).

14. (currently amended) The method of claim 78, wherein said electrochemically depositing an additive material is implemented with an electroplating bath comprising at least one of platinum (Pt), ruthenium (Ru), palladium (Pd), cobalt (Co), and cobalt tungsten (CoW).

15. (original) An extreme ultraviolet lithography (EUVL) mask structure, comprising:

a multilayer (ML) reflective layer formed on a starting substrate;  
a buffer layer formed on said reflective layer;  
an absorber layer formed on said buffer layer, wherein said absorber layer includes an electrochemically deposited additive material on exposed sidewalls during initial etching thereof.

16. (original) The EUVL mask structure of claim 15, The method of claim 8, wherein said electrochemically deposited additive material further comprises an electrolessly deposited material.

17. (original) The EUVL mask structure of claim 15, wherein said electrochemically deposited additive material further comprises an electroplated material.

18. (original) The EUVL mask structure of claim 15, wherein said absorber

layer comprises an optically opaque layer.

19. (original) The EUVL mask structure of claim 15, wherein:  
said absorber layer comprises one of a nickel and a cobalt nickel alloy  
layer; and  
said buffer layer comprises a tantalum nitride layer.

20. (original) The EUVL mask structure of claim 19, wherein said ML  
reflective layer further comprises alternating layers of molybdenum (Mo) and silicon (Si).

21. (original) The EUVL mask structure of claim 15, wherein said  
electrochemically deposited additive material is implemented with an electroplating bath  
comprising at least one of platinum (Pt), ruthenium (Ru), palladium (Pd), cobalt (Co), and  
cobalt tungsten (CoW).